

AMENDMENTS TO THE CLAIMS

Claims 1-13 (Cancelled.)

14. (Original) A method of forming a semiconductor device, the method comprising the steps of:

forming a layer of insulation material over a semiconductor substrate;
forming a layer of conductive material on the layer of insulation material;
etching the layer of conductive material to form a trace, the trace having a top surface; and
etching the trace to form a number of slot openings in the top surface of the trace.

15. (Original) The method of claim 14 wherein the trace is formed to have a number of loops.

16. (Original) The method of claim 15 wherein the loops lie substantially in a same plane.

17. (Original) The method of claim 14 wherein the trace is connected to a contact.

18. (Original) The method of claim 14 wherein the trace is connected to a via.